

isc Silicon NPN Power Transistor

BU2727DX

www.datasheet4u.com

DESCRIPTION

- High Switching Speed
- High Voltage
- Built-in Ddamper Ddiode

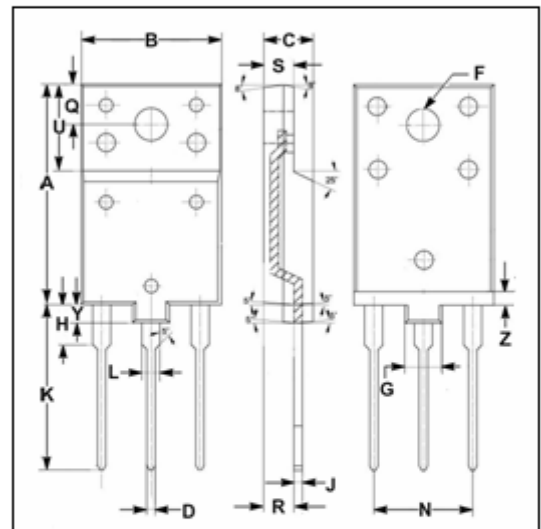
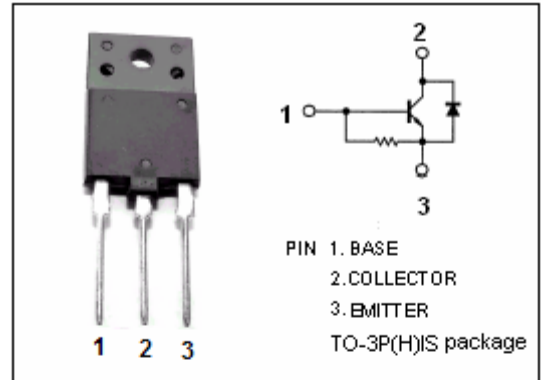
APPLICATIONS

- Designed for use in horizontal deflection circuits of high resolution monitors.

ABSOLUTE MAXIMUM RATINGS(T_a=25°C)

SYMBOL	PARAMETER	VALUE	UNIT
V _{CES}	Collector- Emitter Voltage(V _{BE} = 0)	1700	V
V _{CEO}	Collector-Emitter Voltage	825	V
V _{EBO}	Emitter-Base Voltage	7.5	V
I _C	Collector Current- Continuous	12	A
I _{CM}	Collector Current-Peak	30	A
I _B	Base Current- Continuous	12	A
I _{BM}	Base Current-Peak	20	A
P _C	Collector Power Dissipation @ T _C =25°C	45	W
T _J	Junction Temperature	150	°C
T _{stg}	Storage Temperature Range	-65~150	°C

SYMBOL	PARAMETER	MAX	UNIT
R _{th j-c}	Thermal Resistance,Junction to Case	2.8	°C/W



DIM	mm	
	MIN	MAX
A	24.30	24.70
B	15.20	15.80
C	5.20	5.80
D	0.65	0.85
F	3.30	3.90
G	3.90	4.10
H	4.30	4.70
J	0.80	1.00
K	18.30	18.70
L	1.90	2.10
N	10.70	11.10
Q	4.40	4.60
R	3.30	3.70
S	3.20	3.40
U	9.50	9.70
Y	1.90	2.10
Z	1.40	1.60

isc Silicon NPN Power Transistor**BU2727DX****ELECTRICAL CHARACTERISTICS****T_c=25°C unless otherwise specified**

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)EBO}	Emitter-Base Breakdown Voltage	I _E = 600mA; I _C = 0	7.5			V
V _{CE(sat)}	Collector-Emitter Saturation Voltage	I _C = 5A; I _B = 0.91A			1.0	V
V _{BE(sat)}	Base-Emitter Saturation Voltage	I _C = 5A; I _B = 0.91A			1.0	V
I _{CES}	Collector Cutoff Current	V _{CE} = 1700V; V _{BE} = 0 V _{CE} = 1700V; V _{BE} = 0; T _C =125°C			1.0 2.0	mA
h _{FE-1}	DC Current Gain	I _C = 1A; V _{CE} = 5V		22		
h _{FE-2}	DC Current Gain	I _C = 5A; V _{CE} = 1V	5.5		11	